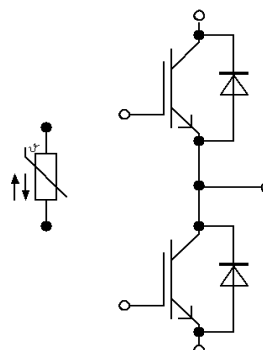
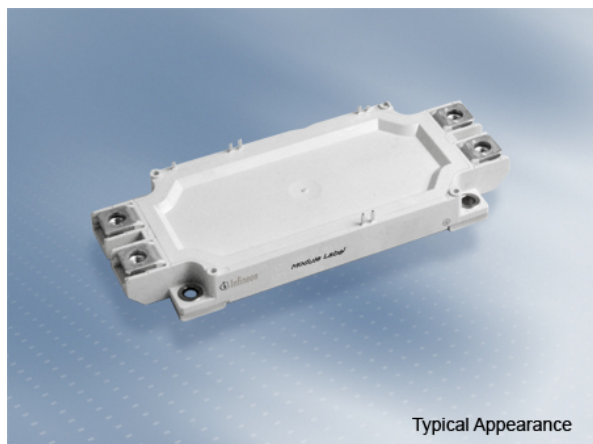


EconoDUAL™3 Modul mit Trench/Feldstopp IGBT4 und Emitter Controlled Diode und NTC / bereits aufgetragenem Thermal Interface Material

EconoDUAL™3 module with Trench/Fieldstop IGBT4 and Emitter Controlled diode and NTC / pre-applied Thermal Interface Material



$V_{CES} = 1700V$
 $I_{C\ nom} = 225A / I_{CRM} = 450A$

Typische Anwendungen

- Motorantriebe
- Servoumrichter
- USV-Systeme
- Windgeneratoren

Elektrische Eigenschaften

- Niedriges V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$

Mechanische Eigenschaften

- Standardgehäuse
- Thermisches Interface Material bereits aufgetragen

Typical Applications

- Motor drives
- Servo drives
- UPS systems
- Wind turbines

Electrical Features

- Low V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$

Mechanical Features

- Standard housing
- Pre-applied Thermal Interface Material

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, Wechselrichter / IGBT, Inverter Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 70^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$	225	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	450	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 225\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 225\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 225\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,95 2,35 2,45	2,30	V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 9,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20 5,80	6,40	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	2,35		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	2,8		Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	18,5		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,60		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		3,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 225\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 3,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,22 0,25 0,26		μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 225\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 3,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,08 0,085 0,09		μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 225\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 6,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,69 0,84 0,88		μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 225\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 6,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,28 0,54 0,62		μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 225\text{ A}, V_{CE} = 900\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 3100\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 3,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	51,0 67,5 72,0		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 225\text{ A}, V_{CE} = 900\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 6,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	45,5 73,5 83,5		mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 1000\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	1100		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}		0,151	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$